



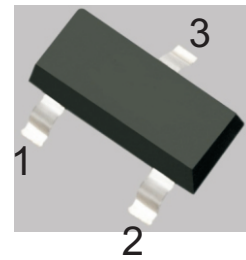
SS8550

PNP TRANSISTOR

FEATURES

- High Collector Current
- Complementary to SS8050

SOT-23



1.BASE
2.EMITTER
3.COLLECTOR

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current — Continuous	I_C	-1.5	A
Collector Dissipation	P_C	200	mW
Thermal Resistance From Junction To Ambient	R_{thJA}	625	°C/W
Operation Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwise noted.)

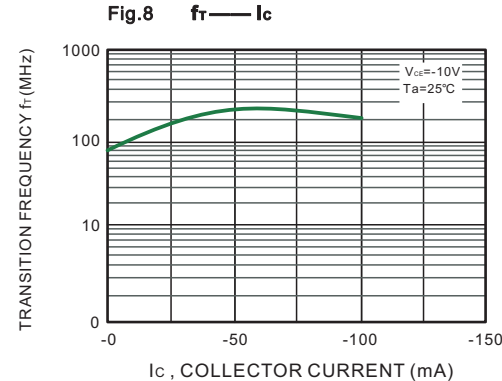
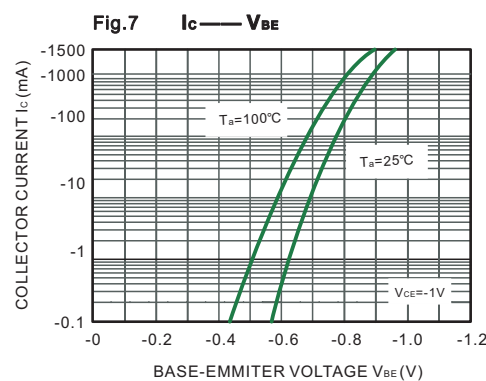
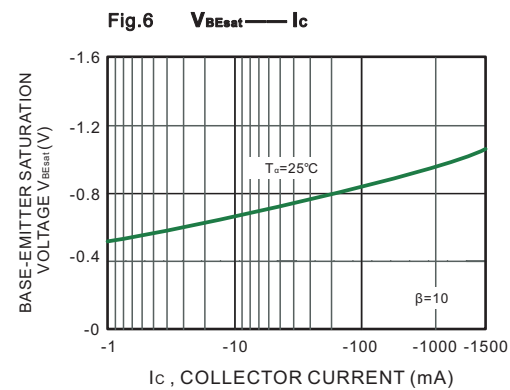
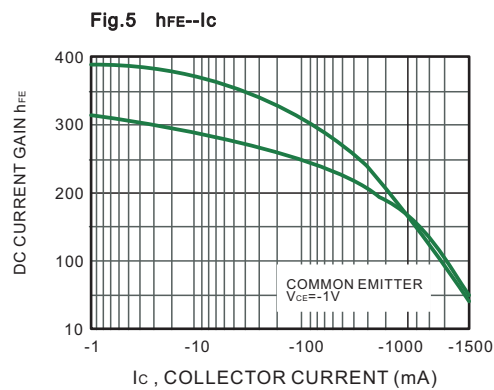
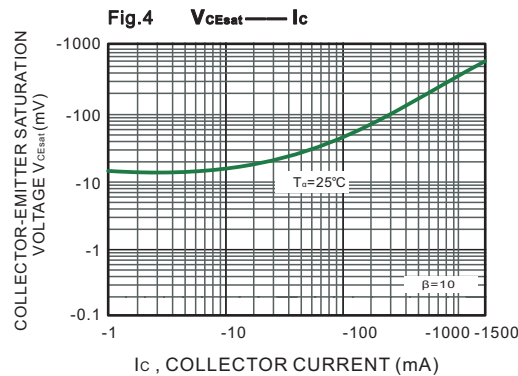
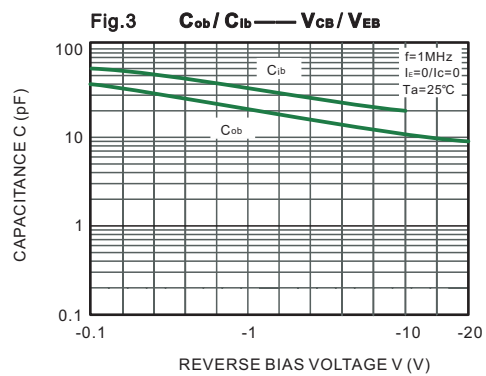
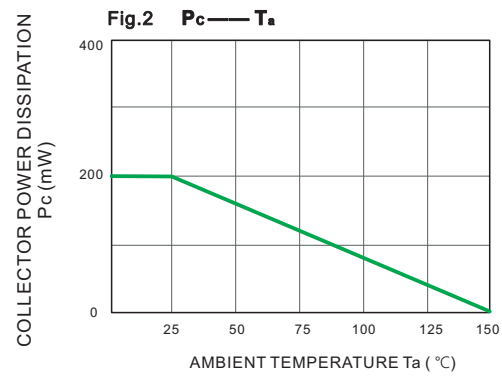
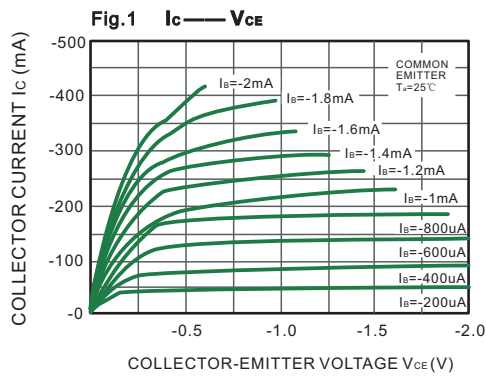
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -0.1 mA, I_B = 0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -40V, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20V, I_B = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC current gain	h_{FE1}	$V_{CE} = -1V, I_C = -100mA$	120		400	
	h_{FE2}	$V_{CE} = -1V, I_C = -800mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -800mA, I_B = -80mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -800mA, I_B = -80mA$			-1.2	V
Base-emitter voltage	V_{BE}	$V_{BE} = -1V, I_C = -10mA$			-1	V
Transition frequency	f_T	$V_{CE} = -10V, I_C = -50mA, f = 30MHz$	100			MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$			20	

CLASSIFICATION OF $h_{FE(1)}$

RANK	L	H	J
RANGE	120-200	200-350	300-400
MARKING	Y2		

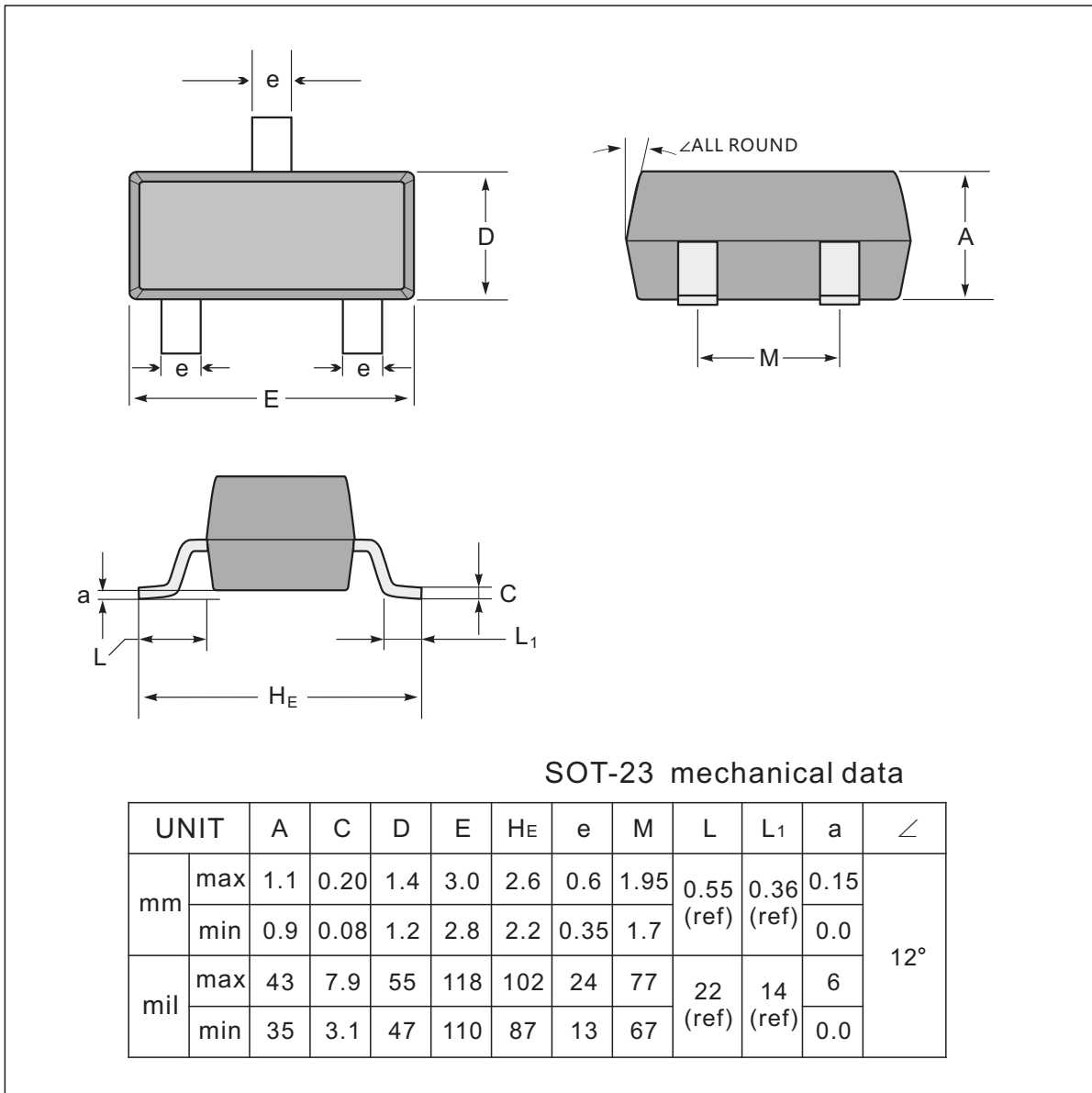


TYPICAL CHARACTERISTICS

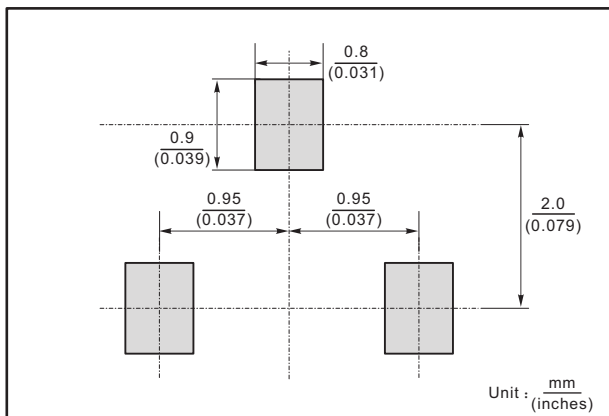




SOT-23 Package Outline Dimensions



The recommended mounting pad size



Marking

Type number	Marking code
SS8550	Y2